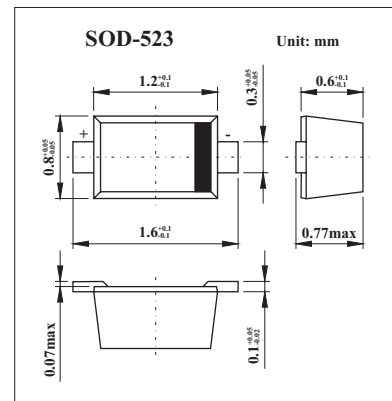


SCHOTTKY BARRIER DIODE

1PS79SB70

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Ultra small plastic SMD package.
- Low capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V_R			70	V
continuous forward current	I_F			70	mA
repetitive peak forward current	I_{FSM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		70	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		100	mA
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			150	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Max	Unit
continuous forward voltage	V_F	$I_F = 1 \text{ mA}$	410	mV
		$I_F = 10 \text{ mA}$	750	mV
		$I_F = 15 \text{ mA}$	1	V
capacitance reverse current	I_R	$V_R = 50 \text{ V}$, note 1	100	nA
		$V_R = 70 \text{ V}$, note 1	10	μA
diodes capacitance	C_d	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	2	pF

Note

1. Pulse test: $t_p = 300 \mu\text{s}$, $\delta = 0.02$.

■ Marking

Marking	G
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